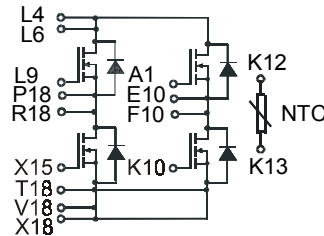


Power MOSFET

in ECO-PAC 2

N-Channel Enhancement Mode
High dv/dt, Low t_{rr} , HDMOS™ Family

PSHM 120/01



I_{D25} = 75 A
 V_{DSS} = 100 V
 R_{DSon} = 25 mΩ
 t_{rr} < 200 ns



Preliminary Data Sheet

MOSFETs

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	100	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	300	A
I_{AR}	$T_C = 25^\circ\text{C}$	75	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	2.0		V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$; $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}$; $T_J = 125^\circ\text{C}$			250 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t < 300\ \mu\text{s}$, duty cycle $d < 2\%$	25		mΩ
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = I_{D25}$, pulse test	25	30	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	4500		pF
C_{oss}		1600		pF
C_{rss}		800		pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$, (External)	20	30	ns
t_r		60	110	ns
$t_{d(off)}$		80	110	ns
t_f		60	90	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 I_{D25}$	180	260	nC
Q_{gs}		36	70	nC
Q_{gd}		85	160	nC
R_{thJC}	with heatsink compound (0.42 K/m.K; 50 μm)		0.5	K/W
R_{thCK}		0.25		K/W

Features

- HiPerFET™ technology
 - low R_{DSon}
 - low gate charge for high frequency operation
 - unclamped inductive switching (UIS) capability
 - dv/dt ruggedness
 - fast intrinsic reverse diode
- ECO-PAC 2 package
 - isolated back surface
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - solderable pins for PCB mounting
- UL registered, E 148688

Applications

- drives and power supplies
- battery or fuel cell powered
- automotive, industrial vehicle etc.
- secondary side of mains power supplies

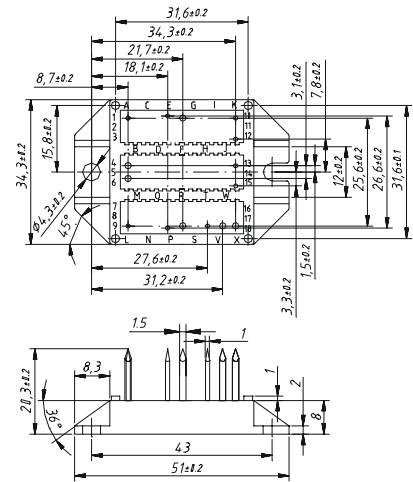
Caution: These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

Source-Drain Diode

Characteristic Values
($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			75 A
I_{SM}	Repetitive;			300 A
V_{SD}	$I_F = I_{D25}$, $V_{GS} = 0\text{ V}$, Pulse test, $t < 300\ \mu\text{s}$, duty cycle $d < 2\%$			1.75 V
t_{rr}	$I_F = 25\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$ $V_R = 25\text{ V}$, $T_J = 125^\circ\text{C}$		300	200 ns ns

Dimensions in mm (1 mm = 0.0394")



Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^\circ\text{C}$	4.75	5.0	5.25 k Ω
$B_{25/50}$			3375	K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz; $t = 1\text{ s}$	3600	V~
M_d	Mounting torque (M4)	1.5 - 2.0	Nm 14 - 18 lb.in.
a	Max. allowable acceleration	50	m/s^2

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d_A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight			24	g

Data according to IEC 60747 refer to a single diode or transistor unless otherwise stated

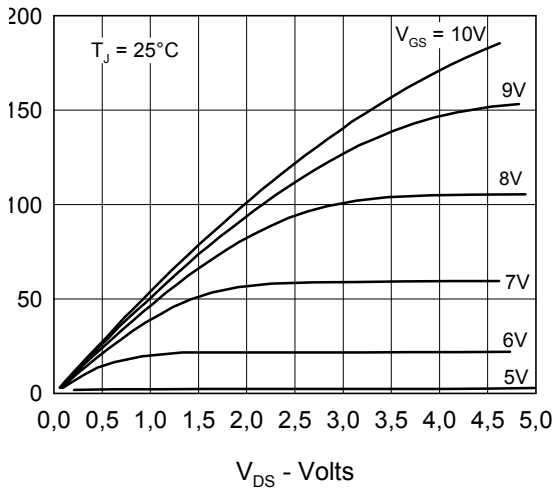


Fig. 1 Output Characteristics

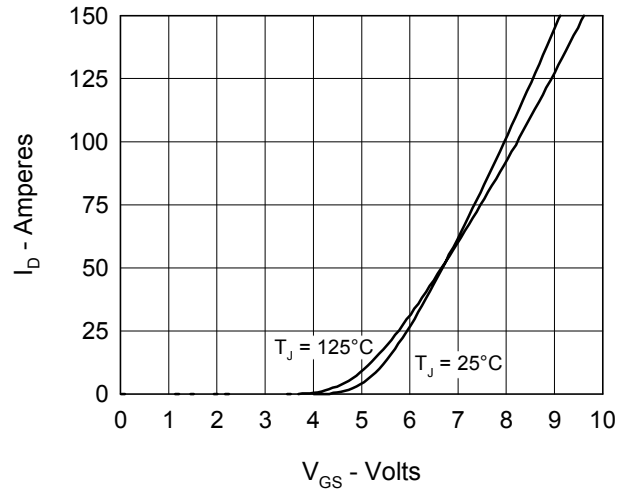


Fig. 2 Input Admittance

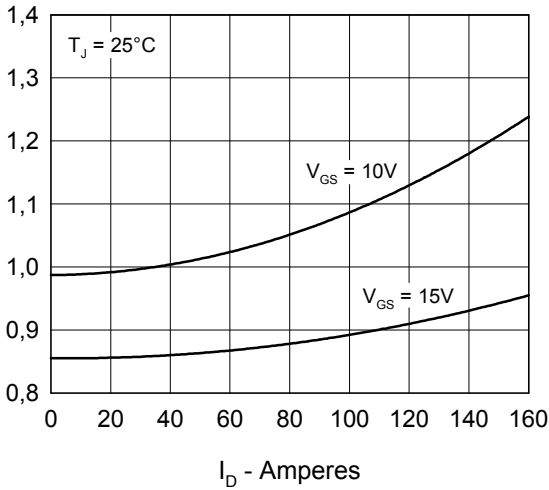


Fig. 3 $R_{DS(on)}$ vs. Drain Current

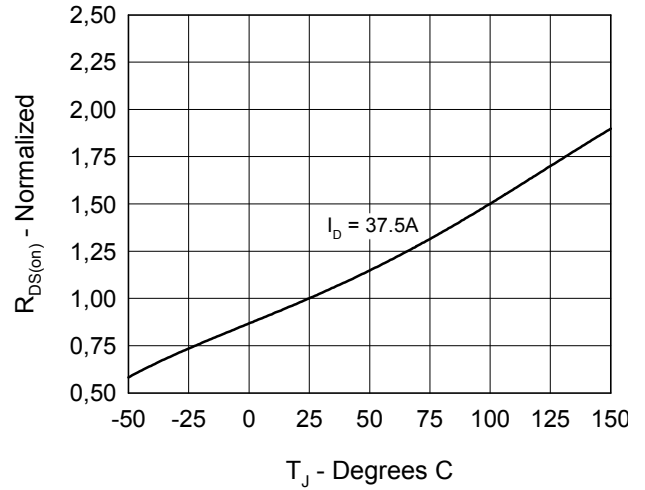


Fig. 4 Temperature Dependence of Drain to Source Resistance

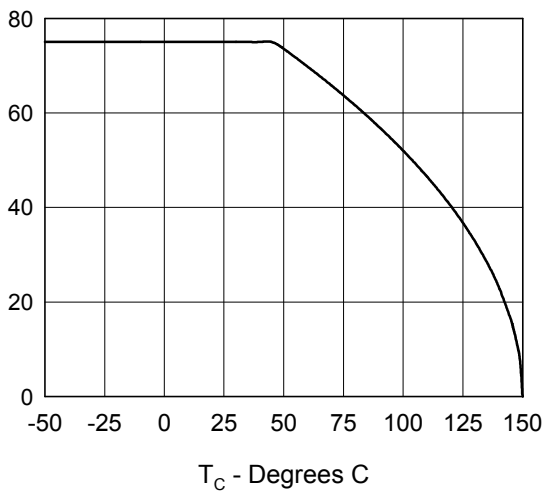


Fig. 5 Drain Current vs. Case Temperature

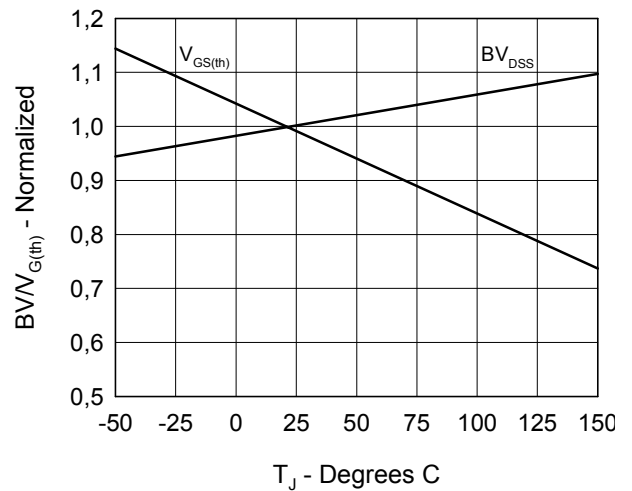


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

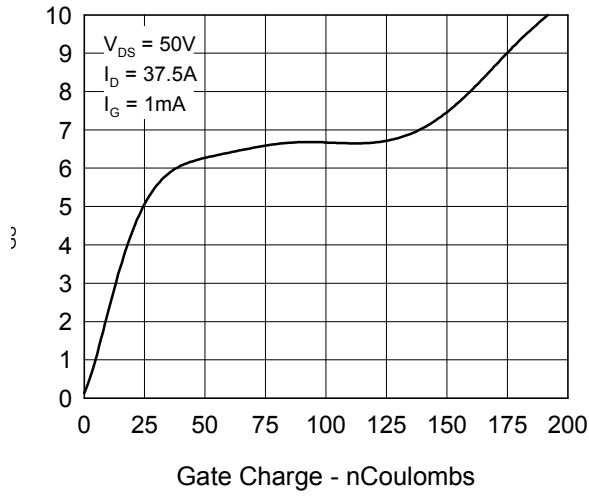


Fig.7 Gate Charge Characteristic Curve

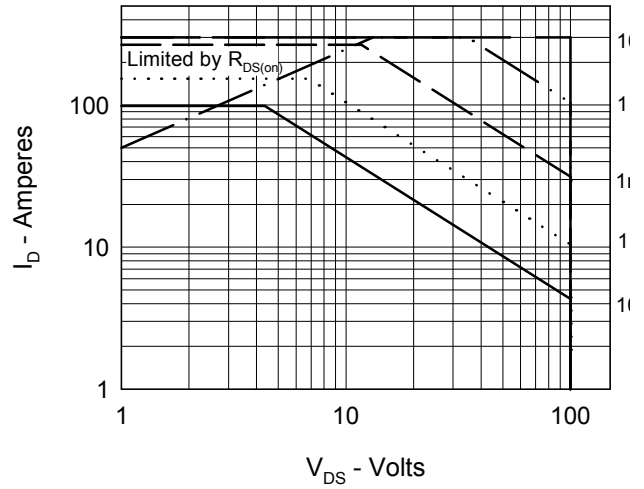


Fig.8 Forward Bias Safe Operating Area

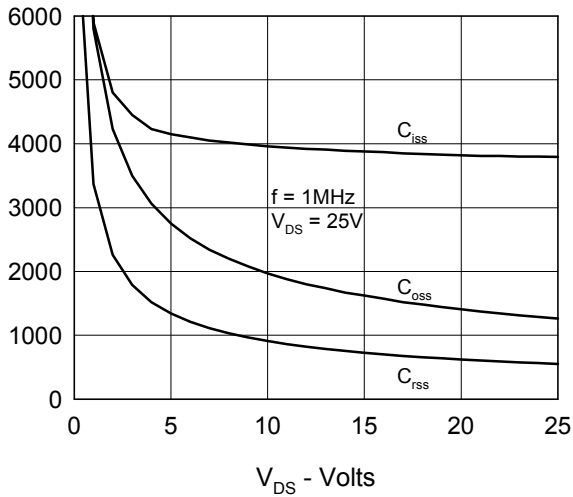


Fig.9 Capacitance Curves

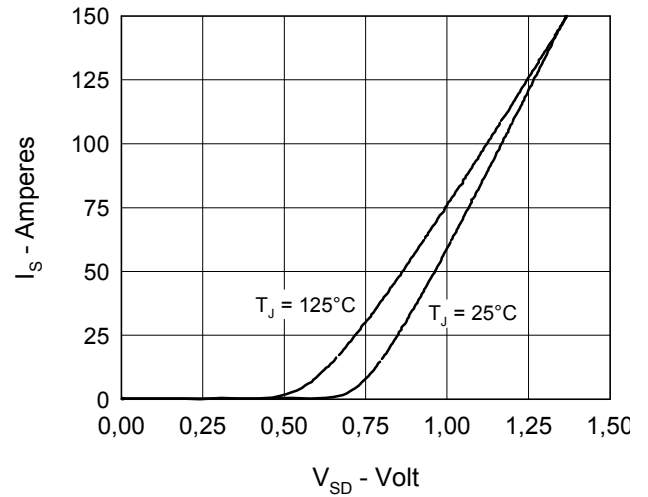


Fig.10 Source Current vs. Source to Drain Voltage

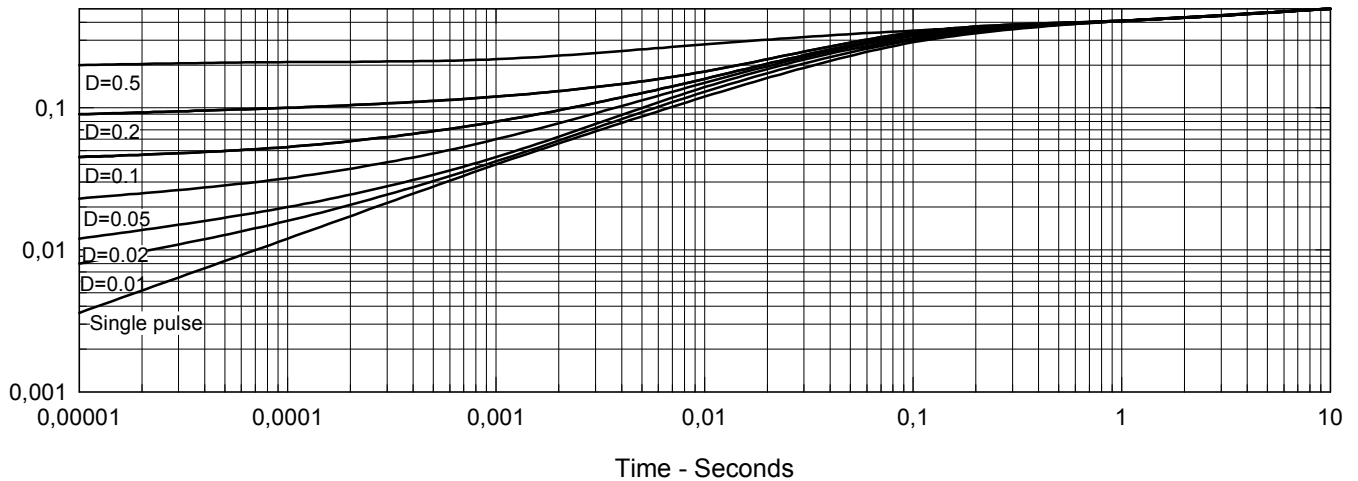


Fig.11 Transient Thermal Impedance